# VS-U5FH120EA120

### **Vishay Semiconductors**



FRED Pt<sup>®</sup> Gen 5 Ultrafast Rectifier Diode, 1200 V, 120 A

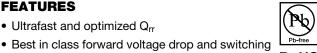


PRIMARY CHARACTERISTICS							
V <sub>R</sub>	1200 V						
V <sub>F</sub> (typical) at 60 A, per diode	1.99 V						
t <sub>rr</sub> (typical) at 60 A, per diode	71 ns						
$I_{F(DC)}$ per module at $T_C = 85 \ ^{\circ}C$	120 A						
Туре	Modules - diode FRED Pt®						
Package	SOT-227						
Circuit configuration	Two separate diodes, antiparallel pin-out						

#### **FEATURES**

losses trade off

Ultrafast and optimized Q<sub>rr</sub>



- RoHS COMPLIANT
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and gualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, the VS-U5FH120FA120 is the right choice for high frequency converters, both soft switched / resonant. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters, and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode voltage	V <sub>R</sub>		1200	V			
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 85 °C	60	۸			
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	340	A			
Maximum power dissipation per module	PD	T <sub>C</sub> = 85 °C	261	W			
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-			
Farmered welters	V <sub>FM</sub>	I <sub>F</sub> = 60 A	-	1.99	2.5	V		
Forward voltage		I <sub>F</sub> = 60 A, T <sub>J</sub> = 150 °C	-	1.74	-			
	I <sub>RM</sub>	V <sub>R</sub> = 1200 V	-	0.4	80			
Reverse leakage current		$T_{\rm J} = 125 \ ^{\circ}{\rm C}, V_{\rm R} = 1200 \ {\rm V}$	-	79	-	μA		
		T <sub>J</sub> = 150 °C, V <sub>R</sub> = 1200 V	-	255	-			

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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Poverse receivery time	t <sub>rr</sub>	$T_J = 25 \ ^\circ C$		-	71	-	ns	
Reverse recovery time		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 60 A, di <sub>F</sub> /dt = 1000 A/μs, V <sub>R</sub> = 800 V	-	114	-		
Doole recovery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	34	-	A	
Peak recovery current		T <sub>J</sub> = 125 °C		-	53	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	2.3	-	μC	
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	5.5	-	μο	
Junction capacitance	CT	V <sub>R</sub> = 1200 V		-	22.5	-	pF	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance junction to case, per diode	D		-	-	0.69		
Thermal resistance junction to case, per module	R <sub>thJC</sub>		-	-	0.345	°C/W	
Thermal resistance case to heatsink, per module	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-		
Weight			-	30	-	g	
		Torque per diode	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style				SOT	-227		



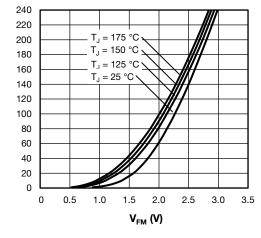


Fig. 1 - Typical Forward Voltage Drop Characteristics

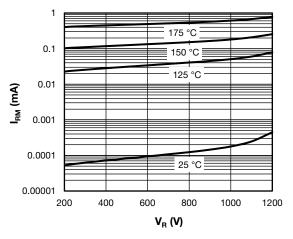


Fig. 2 - Typical Values of Reverse Current



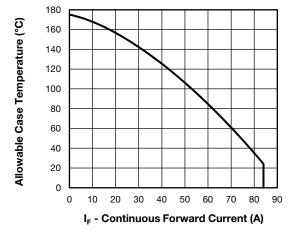


Fig. 3 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Diode)

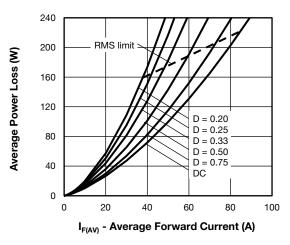


Fig. 4 - Average Power Loss vs. Average Forward Current

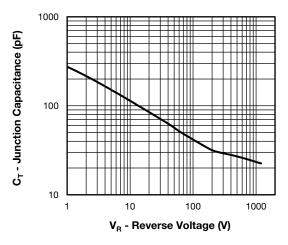


Fig. 5 - Junction Capacitance vs. Reverse Voltage

 $\begin{array}{c}
170\\
160\\
150\\
140\\
130\\
120\\
\end{array}$ 

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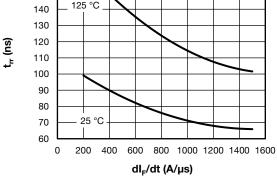


Fig. 6 - Diode Reverse Recovery Time vs. dl<sub>F</sub>dt

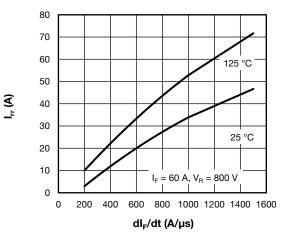


Fig. 7 - Diode Reverse Recovery Current vs. dl<sub>F</sub>dt

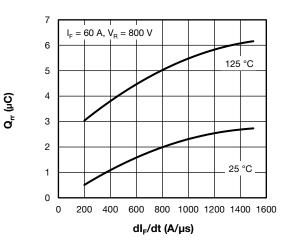


Fig. 8 - Diode Reverse Recovery Charge vs. dl<sub>F</sub>dt

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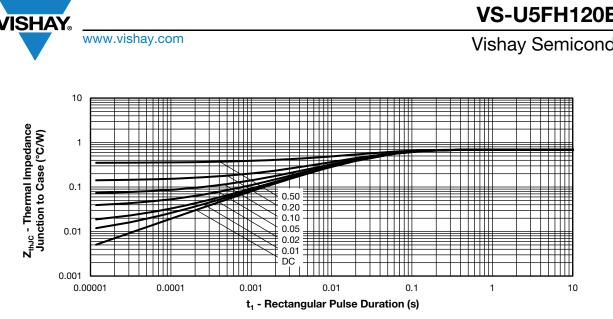


Fig. 9 - Maximum Thermal Impedance Junction to Case

Device code	VS-	U5F	н	120	E	A	120
	1	2	3	4	5	6	7
	1 · 2 ·			niconduo 5 FRED			
	3	• H =	Ultrafas	st FRED	Pt <sup>®</sup> dic	ode	
	4 · 5 ·			ing per r configur			,
	6 7		0	dicator ( ing (120	`		dard ins

CIRCUIT CONFIGURATION								
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
Two separate diodes, antiparallel pin-out	E	Lead Assignment 4 1 1 1 1 1 1 1 1 1 1 1 1 1						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95423					
Packaging information <u>www.vishay.com/doc?95425</u>						
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#### **ORDERING INFORMATION TABLE**

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SOT-227 Generation 2

#### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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